FMS01H350LL

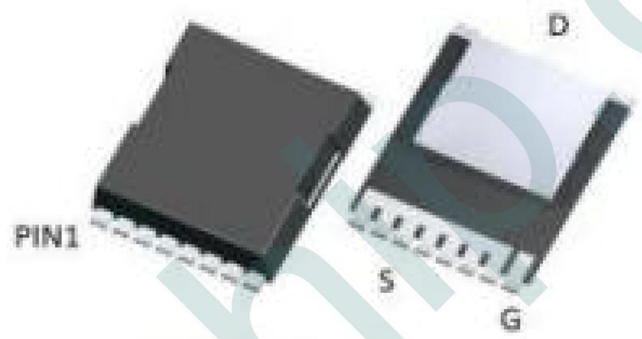
N-Channel SGT Power MOSFET

- 100V,350A
- $R_{DS(ON)}$=1.4mΩ(Typ.) @ V_{GS} =10V
- Advanced SGT Technology
- Provide Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS Tested

Application

- BMS
- Power management
- Load switch
- Motor drivers

Package



TOLL8 top view

Absolute Maximum Ratings (T_C=25℃unless otherwise specified)

Symbol	Parameter		Value	Units
V_{DSS}	Drain-Source Voltage		100	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25℃	350	A
		T_C = 100℃	221	A
I_{DM}	Pulsed Drain Current note1		1400	A
E_{AS}	Single Pulsed Avalanche Energy note2		2162	mJ
P_D	Power Dissipation	T_C = 25℃	380	W
	Derating factor		3.1	W/℃
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	℃

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